

ABSTRACT OF THE DISCLOSURE

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A semiconductor device includes a dicing region provided on a semiconductor substrate to separate a plurality of semiconductor chips each having a gate portion from each other. The semiconductor device further includes a plurality of element isolation regions provided on a surface portion of the semiconductor substrate within the dicing region, a plurality of first dummy patterns formed on a surface of the semiconductor substrate so as to correspond to intervals of the plurality of element isolation regions, respectively, and a plurality of second dummy patterns formed above the semiconductor substrate within the dicing region so as to correspond to the plurality of first dummy patterns, respectively.